



SSC8229GS1

P-Channel Enhancement Mode MOSFET

➤ Features

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	I _D
-20V	±12V	21mΩ@-4V5	-29A
		30mΩ@-2V5	

➤ Description

This device is from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

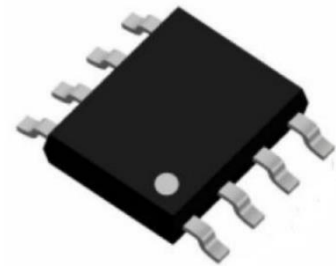
➤ Applications

- Load Switch
- NB battery
- DCDC conversion

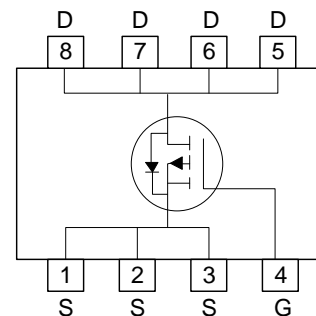
➤ Ordering Information

Device	Package	Shipping
SSC8229GS1	SOP-8	4000/Reel

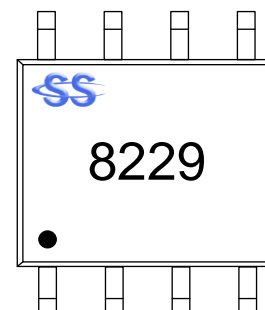
➤ Pin configuration



SOP-8



Pin Configuration (Top View)



Marking (Top View)



➤ **Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-20	V
Gate-to-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current ^c	I_D	-29	A
Continuous Drain Current ^a	I_{DSM}	-7.9	A
Pulsed Drain Current ^b	I_{DM}	-119	A
Power Dissipation ^c	P_D	29.8	W
Power Dissipation ^a	P_{DSM}	2.1	W
Operation junction temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Rated	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	60	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	4.2	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

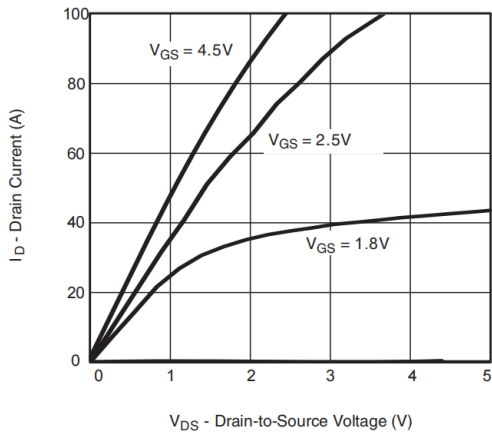


➤ **Electrical Characteristics (T_A=25°C unless otherwise noted)**

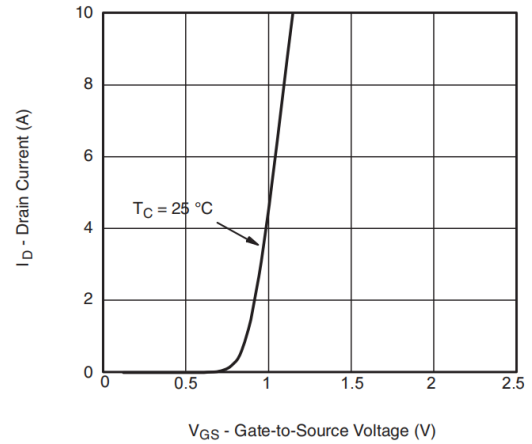
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250uA	-0.5	-0.7	-1	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -12A		21	28	mΩ
		V _{GS} = -2.5V, I _D = -8A		30	40	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V			-1	μA
Gate-Source Leak Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	nA
Transconductance	G _{FS}	V _{DS} = -5V, I _D = -10A		25		s
Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = -1A		-0.75	-1.3	V
Input Capacitance	C _{ISS}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz		1831		pF
Output Capacitance	C _{OSS}			207		
Reverse Transfer Capacitance	C _{RSS}			199		
Total Gate Charge	Q _G	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -12A		84		nC
Gate to Source Charge	Q _{GS}			12		
Gate to Drain Charge	Q _{GD}			20		
Turn-on Delay Time	T _{D(ON)}	V _{GS} = -4.5V, V _{DS} = -10V, R _L = 3Ω, R _G = 1Ω, I _D = -12A		15		ns
Rise Time	T _r			12		
Turn-off Delay Time	T _{D(OFF)}			81		
Fall Time	T _f			68		



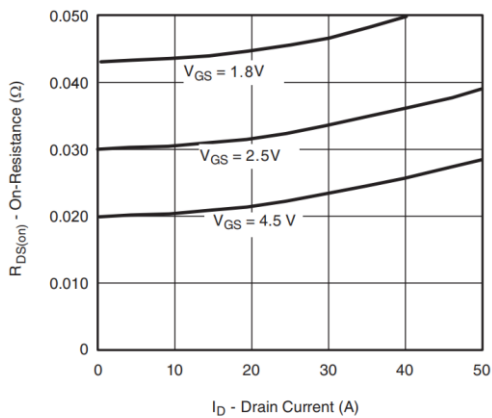
➤ **Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**



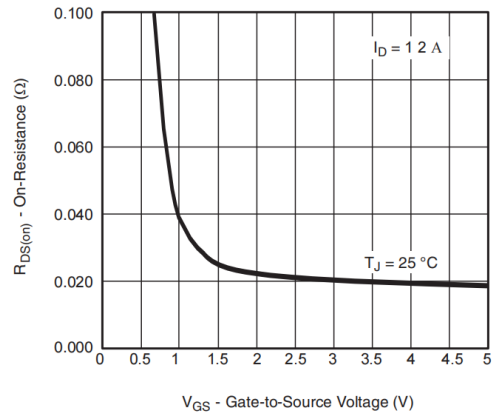
Output Characteristics



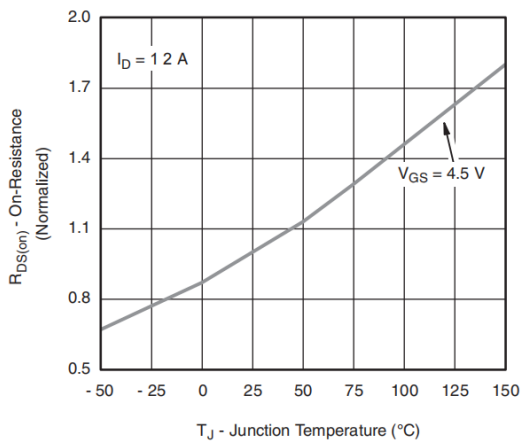
Transfer Characteristics



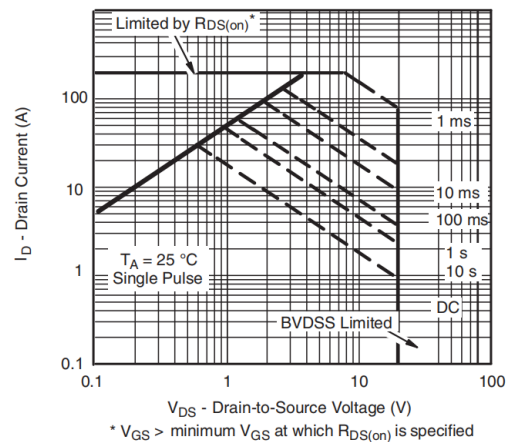
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

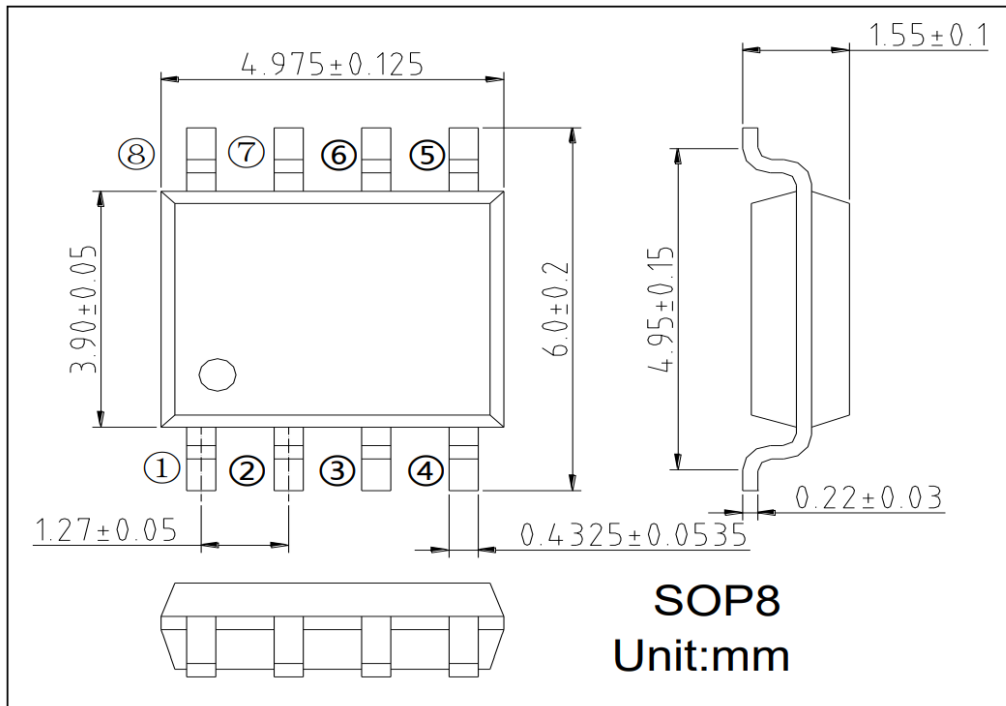


On-Resistance vs. Junction Temperature



Safe Operating Area, Junction-to-Ambient

➤ Package Information



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